



STP36NF06 STP36NF06FP

N-CHANNEL 60V - 0.032 Ω - 30A TO-220/TO-220FP
STripFET™ II POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP36NF06	60 V	<0.040 Ω	30 A
STP36NF06FP	60 V	<0.040 Ω	18 A(*)

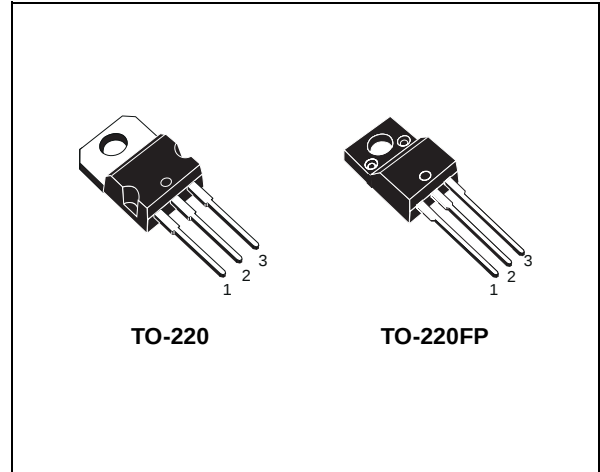
- TYPICAL R_{DS(on)} = 0.032 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- APPLICATION ORIENTED CHARACTERIZATION

DESCRIPTION

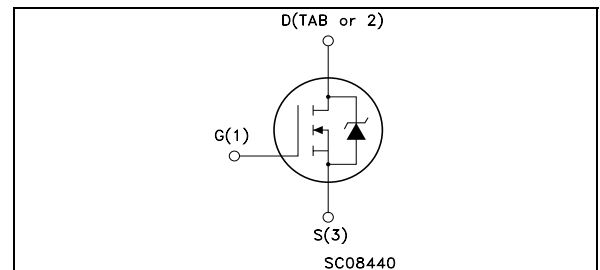
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- AUDIO AMPLIFIERS
- POWER TOOLS
- AUTOMOTIVE ENRIRONMENT



INTERNAL SCHEMATIC DIAGRAM



Ordering Information

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP36NF06	STP36NF06	TO-220	TUBE
STP36NF06FP	STP36NF06FP	TO-220TP	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP36NF06	STP36NF06FP	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	60		V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	60		V
V _{GS}	Gate- source Voltage	± 20		V
I _D	Drain Current (continuous) at T _C = 25°C	30	18(*)	A
I _D	Drain Current (continuous) at T _C = 100°C	21	12	A
I _{DM} (•)	Drain Current (pulsed)	120	72	A
P _{tot}	Total Dissipation at T _C = 25°C	70	25	W
	Derating Factor	0.47	0.17	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	10		V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	200		mJ
T _{stg}	Storage Temperature	-55 to 175		°C
T _j	Max. Operating Junction Temperature			

(•) Pulse width limited by safe operating area.

(*) Current Limited by Package

(1) I_{SD} $\leq$ 120A, di/dt $\leq$ 200A/ μ s, V_{DD} $\leq$ V_{(BR)DSS}, T_j $\leq$ T_{JMAX}

(2) Starting T_j = 25 °C, I_D = 15 A, V_{DD} = 45V

May 2003

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This is preliminary information on a new product now in development or undergoing evaluation. Details are subject to change without notice.

STP36NF06 STP36NF06FP**THERMAL DATA**

			TO-220	TO-220FP	
Rthj-case	Thermal Resistance Junction-case	Max	2.14	6	°C/W
Rthj-amb T _I	Thermal Resistance Junction-ambient Maximum Lead Temperature For Soldering Purpose (1.6 mm from case, for 10 sec)	Max	62.5 300		°C/W °C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	60			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 15 A		0.032	0.040	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 25 V I _D = 15 A		15		S
C _{iss} C _{oss} C _{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		690 170 68		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 18\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		10 40		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 30\text{ V}$ $I_D = 36\text{ A}$ $V_{GS} = 10\text{ V}$		23 6 9	31	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 30\text{ V}$ $I_D = 18\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		27 9		ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				30 120	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 30\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 30\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		65 155 4.8		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(\bullet) Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

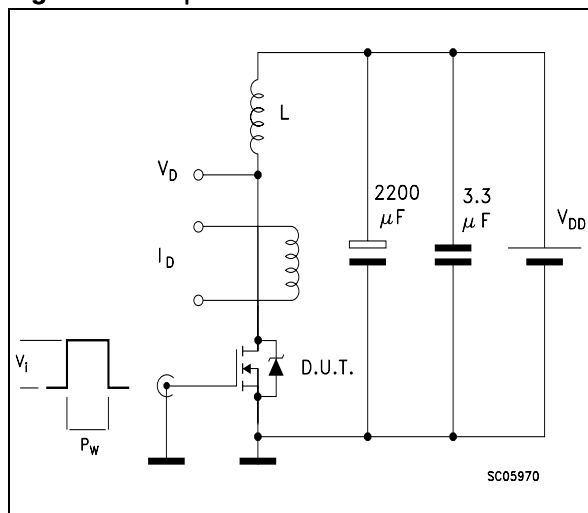


Fig. 2: Unclamped Inductive Waveform

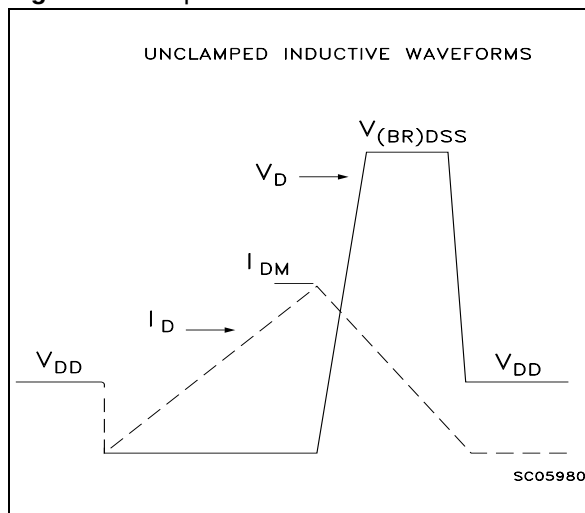


Fig. 3: Switching Times Test Circuits For Resistive Load

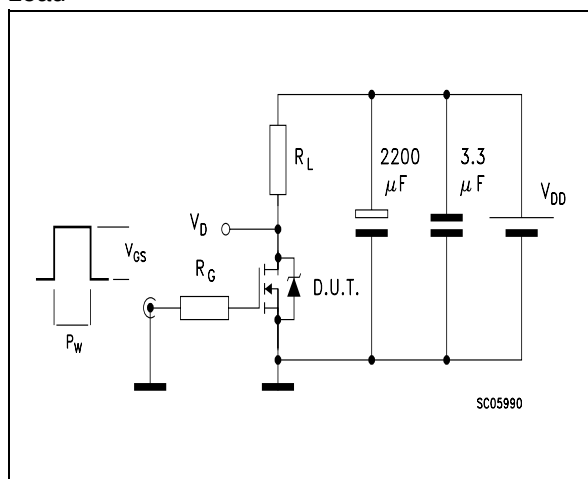


Fig. 4: Gate Charge test Circuit

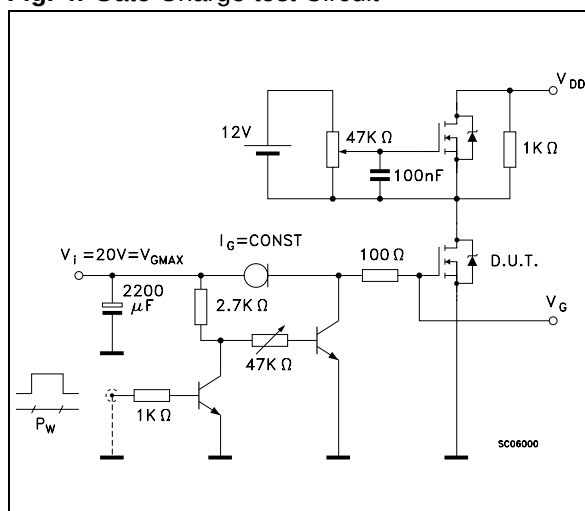
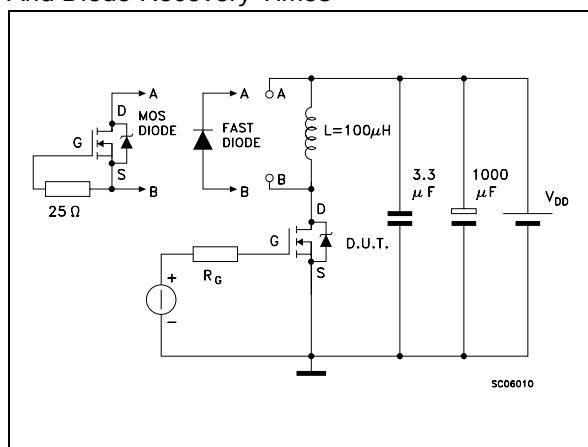
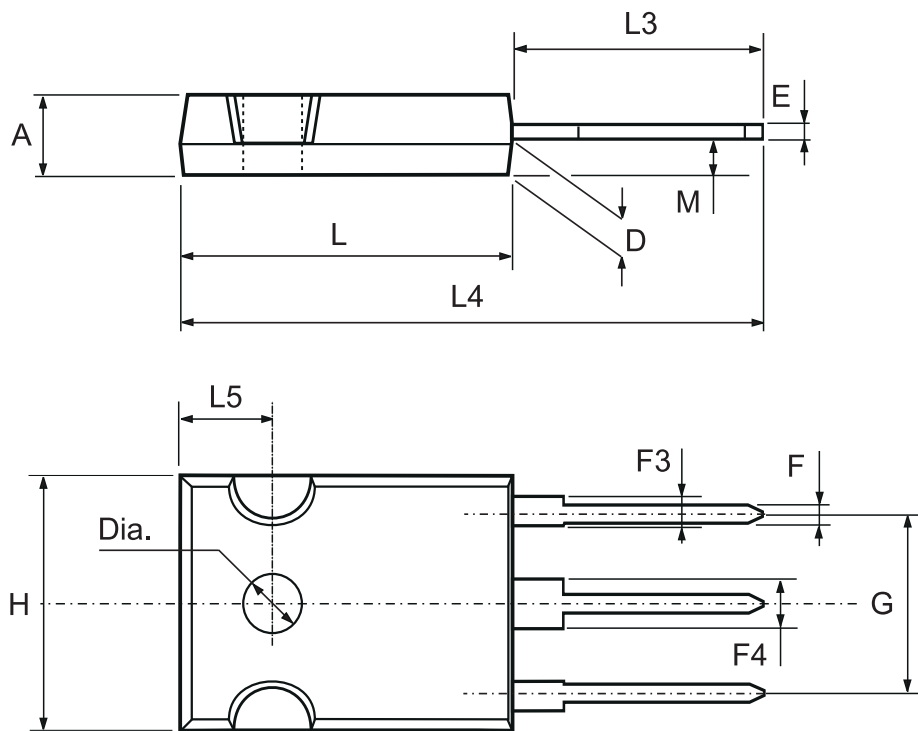


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

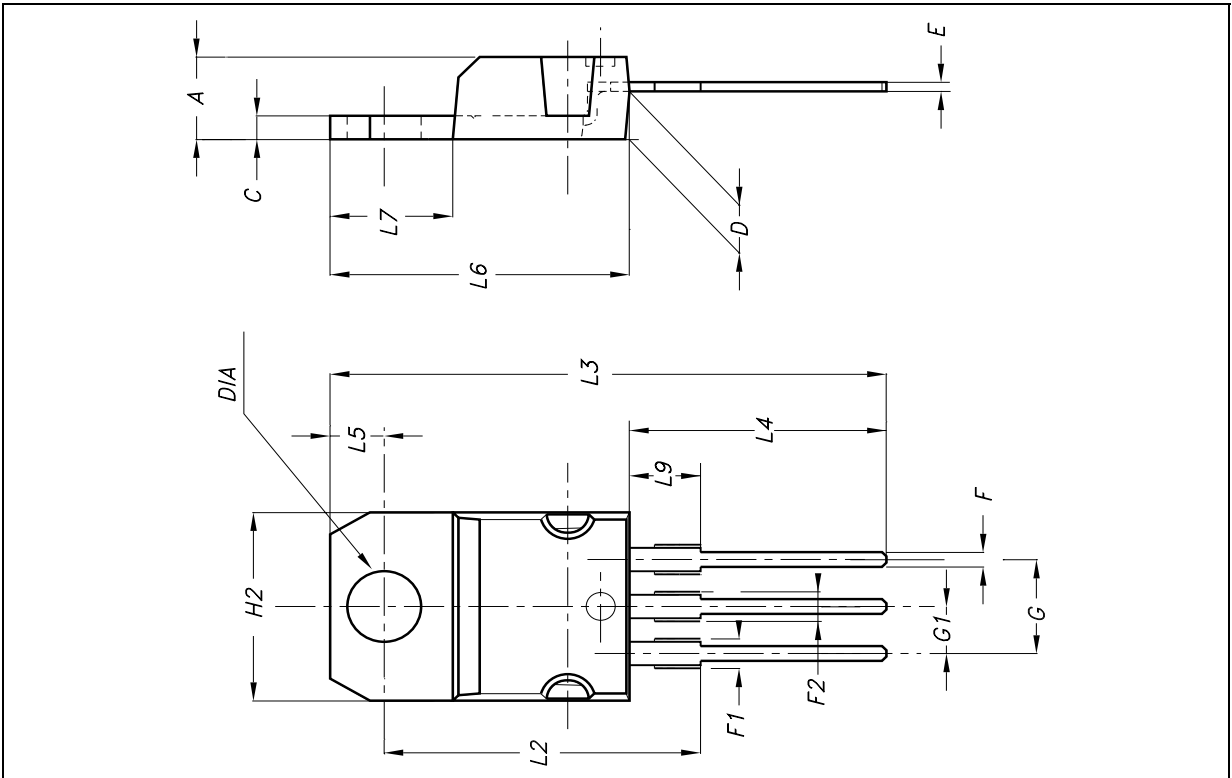
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



P025P

TO-220 MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.40		2.70	0.094		0.106
H2	10		10.40	0.393		0.409
L2		16.40			0.645	
L3		28.90			1.137	
L4	13		14	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
DIA	3.75		3.85	0.147		0.151



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